### LM194/LM394 Supermatch Pair

### **General Description**

The LM194 and LM394 are junction isolated ultra well-matched monolithic NPN transistor pairs with an order of magnitude improvement in matching over conventional transistor pairs. This was accomplished by advanced linear processing and a unique new device structure.

Electrical characteristics of these devices such as drift versus initial offset voltage, noise, and the exponential relationship of base-emitter voltage to collector current closely approach those of a theoretical transistor. Extrinsic emitter and base resistances are much lower than presently available pairs, either monolithic or discrete, giving extremely low noise and theoretical operation over a wide current range. Most parameters are guaranteed over a current range of 1  $\mu \rm A$  to 1 mA and 0V up to 40V collector-base voltage, ensuring superior performance in nearly all applications.

To guarantee long term stability of matching parameters, internal clamp diodes have been added across the emitter-base junction of each transistor. These prevent degradation due to reverse biased emitter current—the most common cause of field failures in matched devices. The parasitic isolation junction formed by the diodes also clamps the substrate region to the most negative emitter to ensure complete isolation between devices.

The LM194 and LM394 will provide a considerable improvement in performance in most applications requiring a closely matched transistor pair. In many cases, trimming can be eliminated entirely, improving reliability and decreasing costs. Additionally, the low noise and high gain make this device attractive even where matching is not critical.

The LM194 and LM394/LM394B/LM394C are available in an isolated header 6-lead TO-5 metal can package. The LM394/LM394B/LM394C are available in an 8-pin plastic dual-in-line package. The LM194 is identical to the LM394 except for tighter electrical specifications and wider temperature range.

#### **Features**

- Emitter-base voltage matched to 50 μV
- Offset voltage drift less than 0.1 µV/°C
- Current gain (hFE) matched to 2%
- Common-mode rejection ratio greater than 120 dB
- $\blacksquare$  Parameters guaranteed over 1  $\mu$ A to 1 mA collector current
- Extremely low noise
- Superior logging characteristics compared to conventional pairs
- Plug-in replacement for presently available devices

### **Typical Applications Low Cost Accurate Square Root Circuit Low Cost Accurate Squaring Circuit** $I_{OUT} = 10^{-5} \cdot \sqrt{10 \, V_{IN}}$ $I_{OUT} = 10^{-6} (V_{IN})^2$ INPUT 100k<sup>4</sup> LM394 150k 1/2 I M394 100 1/2 I M394 1 2k REGULATED TL/H/9241-2 -15V REGULATED TL/H/9241-1 \*Trim for full scale accuracy

### **Absolute Maximum Ratings**

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications. (Note 4)

Collector Current 20 mA Collector-Emitter Voltage  $V_{MAX}$ Collector-Emitter Voltage 35V LM394C 20V Collector-Base Voltage 35V LM394C 20V 35V Collector-Substrate Voltage LM394C 20V Collector-Collector Voltage 35V LM394C

Base-Emitter Current  $\pm\,10~mA$ Power Dissipation 500 mW Junction Temperature LM194  $-55^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$ LM394/LM394B/LM394C  $-25^{\circ}$ C to  $+85^{\circ}$ C Storage Temperature Range  $-65^{\circ}$ C to  $+150^{\circ}$ C Soldering Information Metal Can Package (10 sec.) 260°C Dual-In-Line Package (10 sec.) 260°C Small Outline Package Vapor Phase (60 sec.) 215°C Infrared (15 sec.) 220°C

See AN-450 "Surface Mounting and their Effects on Product Reliability" for other methods of soldering surface

mount devices.

### **Electrical Characteristics** (T<sub>J</sub> = 25°C)

Parameter	Conditions	LM194			LM394			LM394B/394C			Units
raiailletei		Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Oilles
Current Gain (h <sub>FE</sub> )	$\begin{aligned} &V_{CB} = 0V \text{ to } V_{MAX} \text{ (Note 1)} \\ &I_{C} = 1 \text{ mA} \\ &I_{C} = 100  \mu\text{A} \\ &I_{C} = 10  \mu\text{A} \\ &I_{C} = 1  \mu\text{A} \end{aligned}$	350 350 300 200	700 550 450 300		300 250 200 150	700 550 450 300		225 200 150 100	500 400 300 200		
Current Gain Match, (h <sub>FE</sub> Match) $= \frac{100  [\Delta \text{l}_{\text{B}}]  [\text{h}_{\text{FE}(\text{MIN})}]}{\text{l}_{\text{C}}}$	$V_{CB} = 0V$ to $V_{MAX}$ $I_{C} = 10 \mu A$ to 1 mA $I_{C} = 1 \mu A$		0.5 1.0	2		0.5 1.0	4		1.0 2.0	5	% %
Emitter-Base Offset Voltage	$V_{CB} = 0$ $I_{C} = 1 \mu A \text{ to 1 mA}$		25	100		25	150		50	200	μV
Change in Emitter-Base Offset Voltage vs Collector-Base Voltage (CMRR)	(Note 1) $I_{C} = 1 \ \mu \text{A to 1 mA},$ $V_{CB} = 0 \text{V to V}_{MAX}$		10	25		10	50		10	100	μ٧
Change in Emitter-Base Offset Voltage vs Collector Current	$V_{CB}=0V,$ $I_{C}=1~\mu A$ to 0.3 mA		5	25		5	50		5	50	μV
Emitter-Base Offset Voltage Temperature Drift	$I_C = 10 \mu A \text{ to 1 mA (Note 2)}$ $I_{C1} = I_{C2}$ $V_{OS}$ Trimmed to 0 at 25°C		0.08	0.3 0.1		0.08	1.0 0.3		0.2 0.03	1.5 0.5	μV/°C μV/°C
Logging Conformity	$I_C=3$ nA to 300 $\mu$ A, $V_{CB}=0$ , (Note 3)		150			150			150		μV
Collector-Base Leakage	$V_{CB} = V_{MAX}$		0.05	0.25		0.05	0.5		0.05	0.5	nA
Collector-Collector Leakage	$V_{CC} = V_{MAX}$		0.1	2.0		0.1	5.0		0.1	5.0	nA
Input Voltage Noise	$I_{C} = 100 \ \mu A, V_{CB} = 0V,$ f = 100 Hz to 100 kHz		1.8			1.8			1.8		nV/√ <del>Hz</del>
Collector to Emitter Saturation Voltage	$I_{C} = 1 \text{ mA}, I_{B} = 10 \mu A$ $I_{C} = 1 \text{ mA}, I_{B} = 100 \mu A$		0.2 0.1			0.2 0.1			0.2 0.1		V V

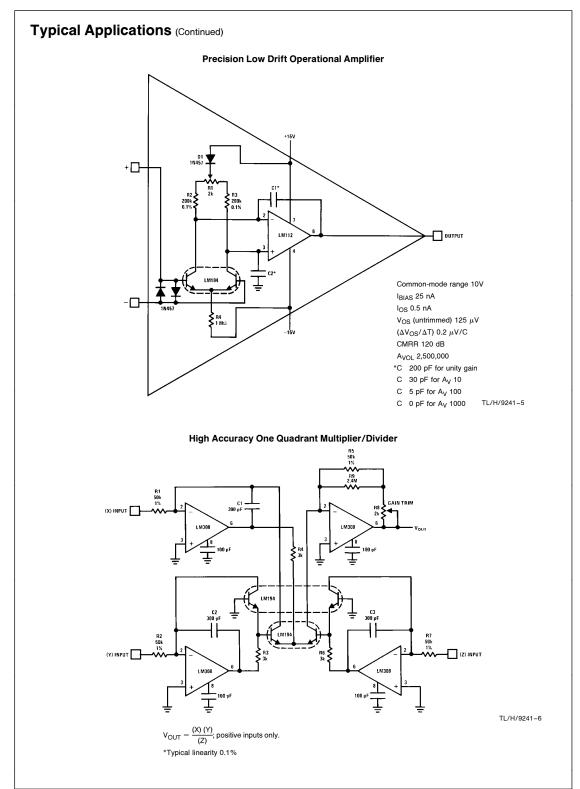
Note 1: Collector-base voltage is swept from 0 to  $V_{MAX}$  at a collector current of 1  $\mu$ A, 10  $\mu$ A, 100  $\mu$ A, and 1 mA.

Note 2: Offset voltage drift with  $V_{OS} = 0$  at  $T_A = 25^{\circ}$ C is valid only when the ratio of  $I_{C1}$  to  $I_{C2}$  is adjusted to give the initial zero offset. This ratio must be held to within 0.003% over the entire temperature range. Measurements taken at  $+25^{\circ}$ C and temperature extremes.

Note 3: Logging conformity is measured by computing the best fit to a true exponential and expressing the error as a base-emitter voltage deviation.

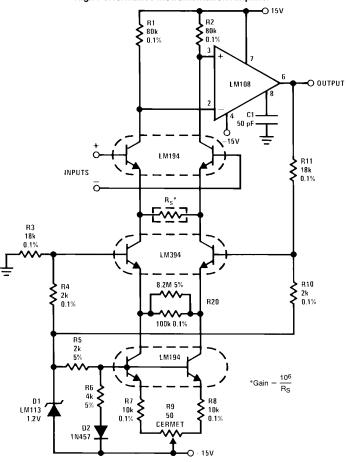
Note 4: Refer to RETS194X drawing of military LM194H version for specifications.

# **Typical Applications** (Continued) Fast, Accurate Logging Amplifier, $V_{\mbox{\scriptsize IN}}=10\mbox{\scriptsize V}$ to 0.1 mV or $I_{\mbox{\scriptsize IN}}=1$ mA to 10 nA R6 9.76k 1% 100k**≯** R2 100 $v_{\text{OUT}}$ TL/H/9241-3 \*1 k $\Omega$ (±1%) at 25°C, +3500 ppm/°C. Available from Vishay Ultronix, Grand Junction, CO, Q81 Series. $V_{OUT} = - log_{10} \left( \frac{V_{IN}}{V_{REF}} \right)$ Voltage Controlled Variable Gain Amplifier 2N3810 LM394 D1 1N457 C1 30 pF **≯**R8\* INPUT LM318 D2 1N457 TL/H/9241-4



### Typical Applications (Continued)

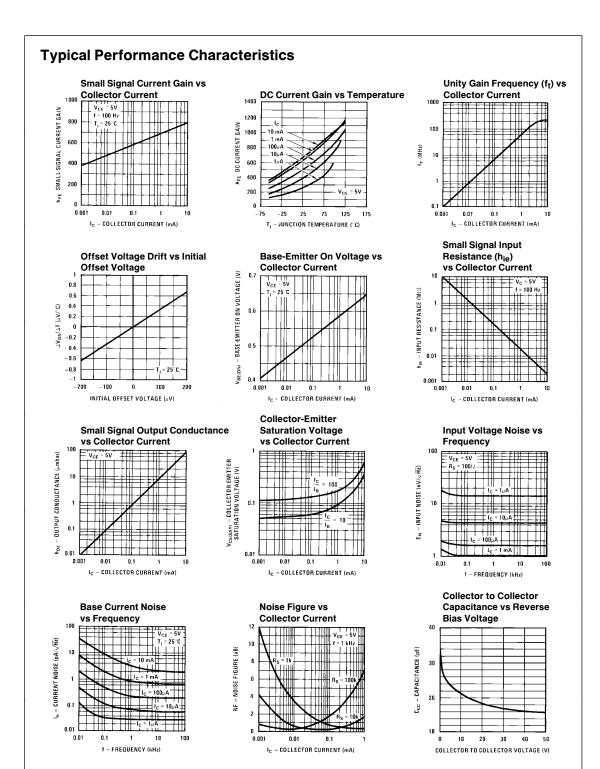
### High Performance Instrumentation Amplifier



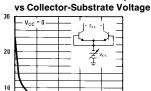
TL/H/9241-7

#### **Performance Characteristics**

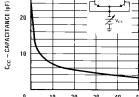
•	G = 10,000 G = 1,000 G = 100 G = 10						
Linearity of Gain ( $\pm$ 10V Output)	≤0.01	≤0.01	≤0.02	≤0.05	%		
Common-Mode Rejection Ratio (60 Hz)	≥120	≥120	≥110	≥90	dB		
Common-Mode Rejection Ratio (1 kHz)	≥110	≥110	≥90	≥70	dB		
Power Supply Rejection Ratio							
+ Supply	>110	>110	>110	>110	dB		
─Supply	>110	>110	>90	>70	dB		
Bandwidth (-3 dB)	50	50	50	50	kHz		
Slew Rate	0.3	0.3	0.3	0.3	V/μs		
Offset Voltage Drift**	≤0.25	≤0.4	2	≤10	μV/°C		
Common-Mode Input Resistance	>109	>109	>109	>109	$\Omega$		
Differential Input Resistance	>3 x 108	>3 x 108	$> 3 \times 10^8$	$>3 \times 10^{8}$			
Input Referred Noise (100 Hz $\leq$ f $\leq$ 10 kHz)	5	6	12	70	$\frac{\text{nV}}{\sqrt{\text{Hz}}}$		
Input Bias Current	75	75	75	75	nΑ		
Input Offset Current	1.5	1.5	1.5	1.5	nΑ		
Common-Mode Range	±11	±11	±11	±10	V		
Output Swing ( $R_L = 10 \text{ k}\Omega$ )	±13	$\pm13$	$\pm13$	$\pm 13$	V		
**Assumes < 5 ppm/°C tracking of resistors							

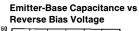


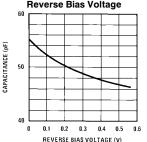
### **Typical Performance Characteristics** (Continued)

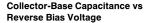


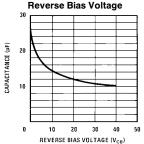
**Collector to Collector Capacitance** 





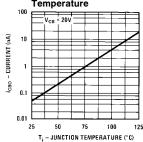




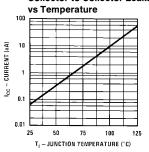


#### Collector-Base Leakage vs **Temperature**

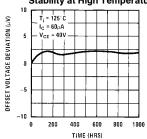
COLLECTOR TO SUBSTRATE VOLTAGE (V)



### **Collector to Collector Leakage**

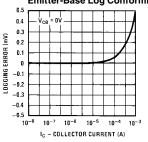


#### Offset Voltage Long Term Stability at High Temperature



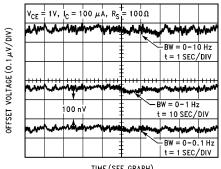
TL/H/9241-9

#### **Emitter-Base Log Conformity**



TL/H/9241-10

#### Low Frequency Noise of Differential Pair\*



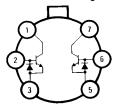
TIME (SEE GRAPH)

\*Unit must be in still air environment so that differential lead temperature is held to less than 0.0003°C.

TL/H/9241-11

### **Connection Diagrams**

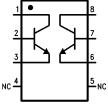
Metal Can Package



Top View

TL/H/9241-12

Order Number LM194H/883\*, LM394H, LM394BH or LM394CH See NS Package Number H06C **Dual-In-Line and Small Outline Packages** 



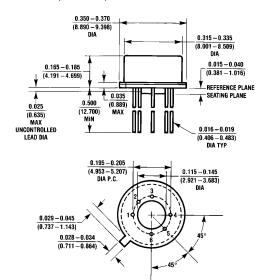
**Top View** 

TL/H/9241-13

Order Number LM394N or LM394CN See NS Package Number N08E

\*Available per SMD #5962-8777701

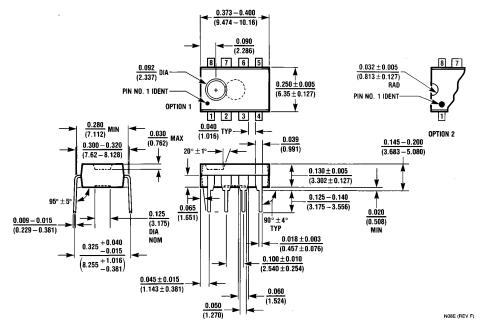




H06C (REV D)

Metal Can Package (H) Order Number LM194H/883, LM394H, LM394BH or LM394CH NS Package Number H06C

### Physical Dimensions inches (millimeters) (Continued)



Molded Dual-In-Line Package (N) Order Number LM394CN or LM394N NS Package Number N08E

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